Method For SONOS EFLASH Integrated Circuit

Abstract

A method of manufacturing a charge storage layer for a SONOS memory device. A feature of the embodiment is the first gate layer is formed over the charge storing layer (ONO) before the charge storing layer is patterned. The first gate layer protects the charge storing layer (ONO) from various etches used in the process to pattern the various gate dielectric layers on other regions of substrate.

Figure 10